RF Micro Devices(R) Expands Family of GaN Unmatched Power Transistors

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GREENSBORO, N.C., Nov. 9, 2010 (GLOBE NEWSWIRE) -- RF Micro Devices, Inc. (Nasdaq:RFMD), a global leader in the design and manufacture of high-performance radio frequency components and compound semiconductor technologies, today announced that RFMD® has production released the RF3932, a 75-watt, highly efficient gallium nitride (GaN) RF unmatched power transistor (UPT) that delivers superior performance versus competing GaAs and silicon power technologies.

The release of the RF3932 follows the recent release of the 140-watt RF3934, which is the highest output power device in RFMD's UPT family. RFMD plans to release a third GaN UPT device in the first calendar quarter of 2011, significantly expanding the GaN power transistor options available to RFMD's customers.

RFMD's GaN unmatched power transistors support "green" architectures that reduce energy consumption, improve thermal management and optimize network efficiency for network operators. The RF3932 operates over a broad frequency range (DC to 3GHz) and delivers high peak efficiency of >65%. Additionally, the RF3932 incorporates simple, optimized matching networks external to the package, providing wideband gain and power performance advantages in a single amplifier. The RF3932 is packaged in a hermetic, flanged ceramic two-leaded package that leverages RFMD's advanced heat sink and power dissipation technologies to deliver excellent thermal stability and conductivity. The 75-watt RF3932 and the 140-watt RF3934 are optimal for both driver and/or output stages, depending on overall power requirements.

Bob Van Buskirk, President of RFMD's Multi-Market Products Group (MPG), said, "RFMD is very pleased to expand our GaN-based product portfolio, offering industry-leading power performance in support of diverse end markets. RFMD's GaN product portfolio clearly demonstrates our commitment to technology and product leadership, and we look forward to introducing additional GaN devices that feature superior power density, high efficiency, rugged dependability and 'green' power consumption advantages."

RFMD's 48-volt, high power-density GaN semiconductor process features high RF power density and efficiency, low capacitance, and high thermal conductivity. This unique combination of features enables the development of compact and efficient high power amplifiers (HPAs) for a broad range of applications, including private mobile radio (PMR), 3G/4G wireless infrastructure, ISM (industrial scientific & medical), military and civilian radar and CATV transmission networks

RFMD will showcase a broad portfolio of industry-leading RF components at the electronica 2010 trade show in Munich Germany, November 9 through November 12. Product brochures will be available at the RFMD booth (#A4.136), and datasheets can be obtained via RFMD's website at www.rfmd.com or by contacting RFMD at 336-664-1233.

Availability

The RF3932 is currently available for sampling and mass production.

About RFMD

RF Micro Devices, Inc. (Nasdaq:RFMD) is a global leader in the design and manufacture of high-performance semiconductor components. RFMD's products enable worldwide mobility, provide enhanced connectivity and support advanced functionality in the cellular handset, wireless infrastructure, wireless local area network (WLAN), CATV/broadband and aerospace and defense markets. RFMD is recognized for its diverse portfolio of semiconductor technologies and RF systems expertise and is a preferred supplier to the world's leading mobile device, customer premises and communications equipment providers.

Headquartered in Greensboro, N.C., RFMD is an ISO 9001- and ISO 14001-certified manufacturer with worldwide engineering, design, sales and service facilities. RFMD is traded on the NASDAQ Global Select Market under the symbol RFMD. For more information, please visit RFMD's web site at www.rfmd.com.

The RF Micro Devices, Inc. logo is available at http://www.globenewswire.com/newsroom/prs/?pkgid=6436

This press release includes "forward-looking statements" within the meaning of the safe harbor provisions of the Private Securities Litigation Reform Act of 1995. These forward-looking statements include, but are not limited to, statements about our plans, objectives, representations and contentions and are not historical facts and typically are identified by use of terms such as "may," "will," "should," "could," "expect," "plan," "anticipate," "believe," "estimate," "predict," "potential," "continue" and similar words, although some forward-looking statements are expressed differently. You should be aware that the forward-looking statements included herein represent management's current judgment and expectations, but our actual results, events and performance could differ materially from those expressed or implied by forward-looking statements. We do not intend to update any of these forward-looking statements or publicly announce the results of any revisions to these forward-looking statements, other than as is required under the federal securities laws. RF Micro Devices' business is subject to numerous risks and uncertainties, including variability in operating results, risks associated with the impact of global macroeconomic and credit conditions on our business and the business of our suppliers and customers, our reliance on a few large customers for a substantial portion of our revenue, the rate of growth and development of wireless markets, our ability to bring new products to market, our reliance on inclusion in third party reference designs for a portion of our revenue, our ability to manage channel partner and customer relationships, risks associated with the operation of our wafer fabrication, molecular beam epitaxy, assembly and test and tape and reel facilities, our ability to complete acquisitions and integrate acquired companies, including the risk that we may not realize expected synergies from our business combinations, our ability to attract and retain skilled personnel and develop leaders, variability in production yields, raw material costs and availability, our ability to reduce costs and improve margins in response to declining average selling prices, our ability to adjust production capacity in a timely fashion in response to changes in demand for our products, dependence on gallium arsenide (GaAs) for the majority of our products, dependence on third parties, and substantial reliance on international sales and operations. These and other risks and uncertainties, which are

described in more detail in RF Micro Devices' most recent Annual Report on Form 10-K and other reports and statements filed with the Securities and Exchange Commission, could cause actual results and developments to be materially different from those expressed or implied by any of these forward-looking statements.

CONTACT: RF Micro Devices, Inc.

Douglas DeLieto, VP of Investor Relations

336-678-7088

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